

# **Graphene based integrated photonics for optical interconnect**

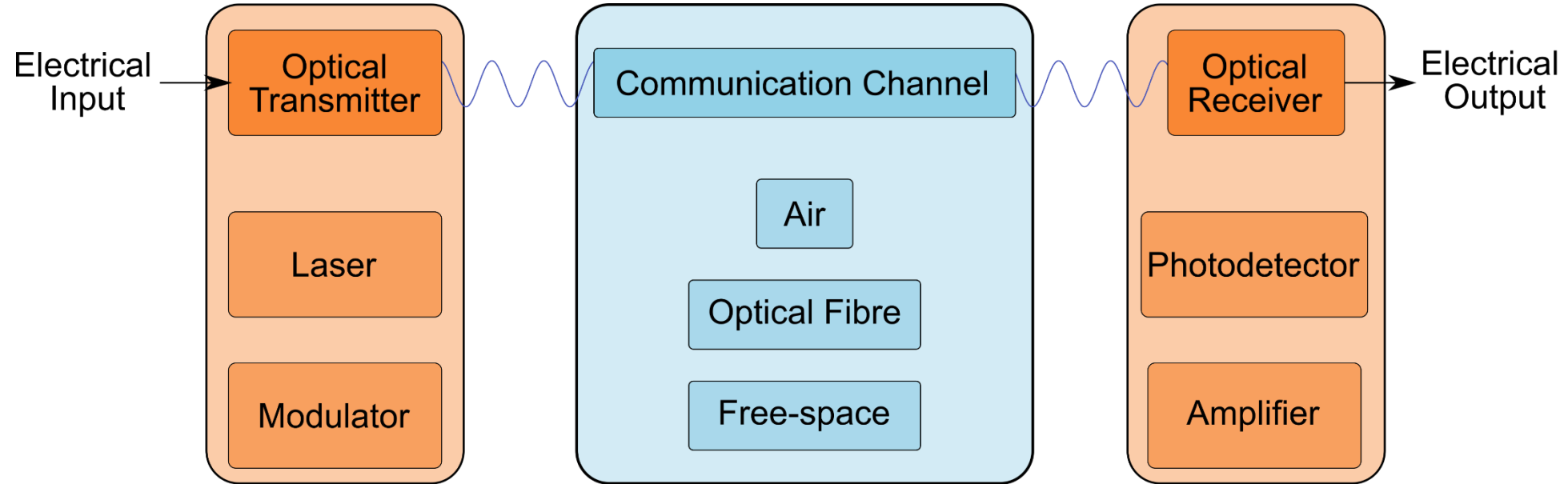
H. F. Y. Watson, A. Ruocco, J. E. Muench, and A. C. Ferrari  
Cambridge Graphene Centre

# Outline

- Optical Links
  - Long-reach optical networks
  - Short-reach optical networks
- Si Photonics
- Graphene for opto-electronics
- Graphene transceiver
- Outlook

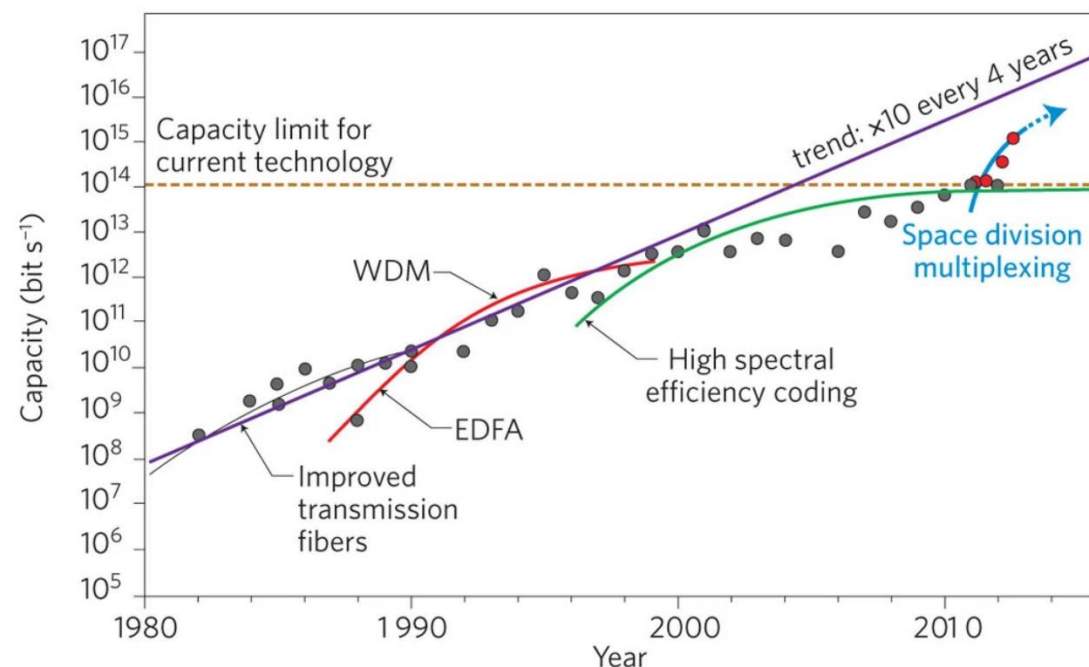


# Optical Links



- Optics enables high-bandwidth and low-power data transmission
- Most expensive component is electro-optic conversion (usually discrete component)

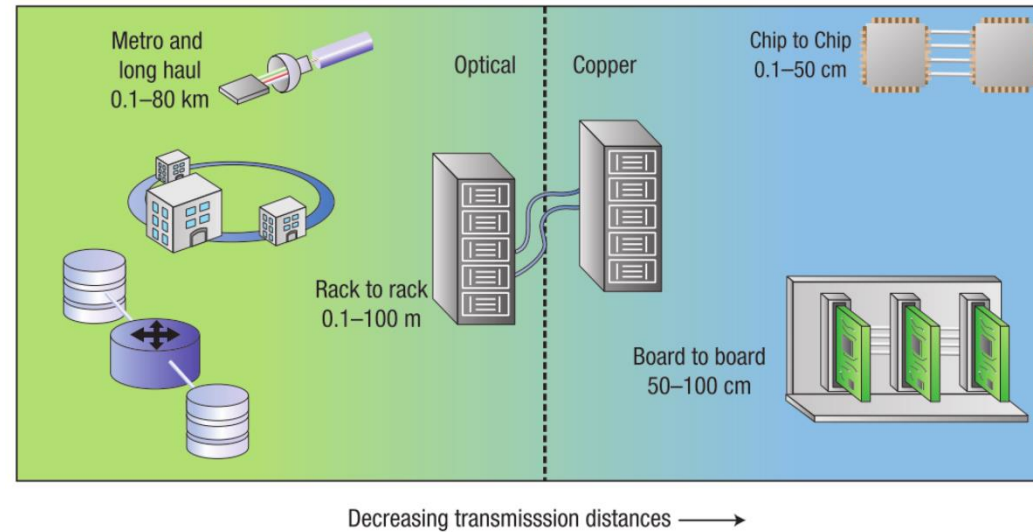
# Long-haul Optical Networks



Richardson, D. J., *et al. Nature Photonics*, 7(5), 354–362 (2013)

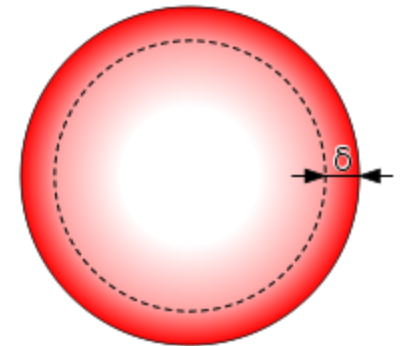
- Optical transmission since 1980s to overcome loss of electrical cables over long distances
  - Driven by the development of low-loss optical fibre and optical amplifiers
- Data rates have continued to rise with adoption of wavelength division multiplexing (WDM), and complex modulation formats
- Hitting the limit to how much data you can send down a single optical fibre (10 Pb/s in 2017)
- **Low-power** optical transceivers needed

# Short-reach Optical Networks



Alduino, A., et al. *Nature Photonics*, 1(3), 153–155 (2007)

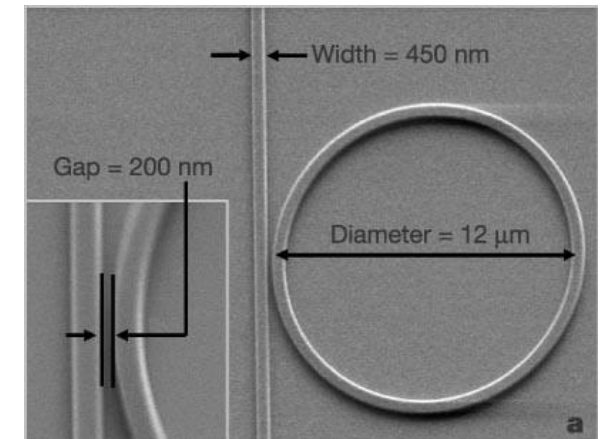
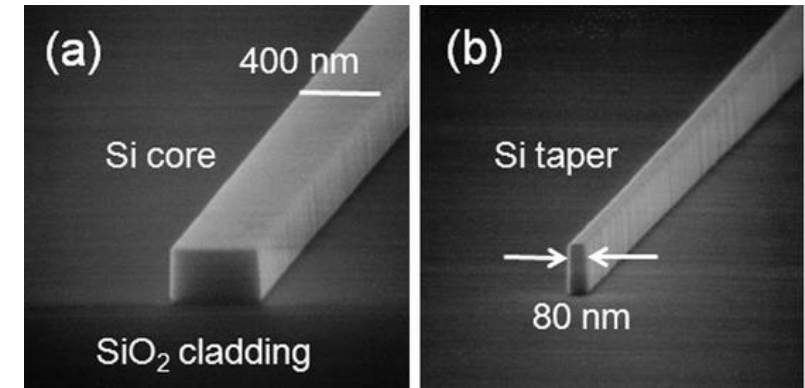
Resistance of electrical interconnects  $\propto \sqrt{f}$  due to the skin effect



- Losses of electrical interfaces will become unmanageable at Tb/s data rates, making optical interconnect worth the cost
- **Low-power** and **compact** optical transceivers needed

# Si Photonics

- Photonic circuits made of submicron Si waveguides guide light on-chip
- Fabricated with existing CMOS technology
- Si band gap (1.1 eV at 300 K) makes Si transparent for  $\lambda = 1.3 - 1.55 \mu\text{m}$
- Ideal for guiding light with low optical loss, but not good for modulators and photodetectors that interact with light...



Xu, Q., et al. *Nature* **435**, 325–327 (2005)



# Si Photonics

## Pluggable Optics

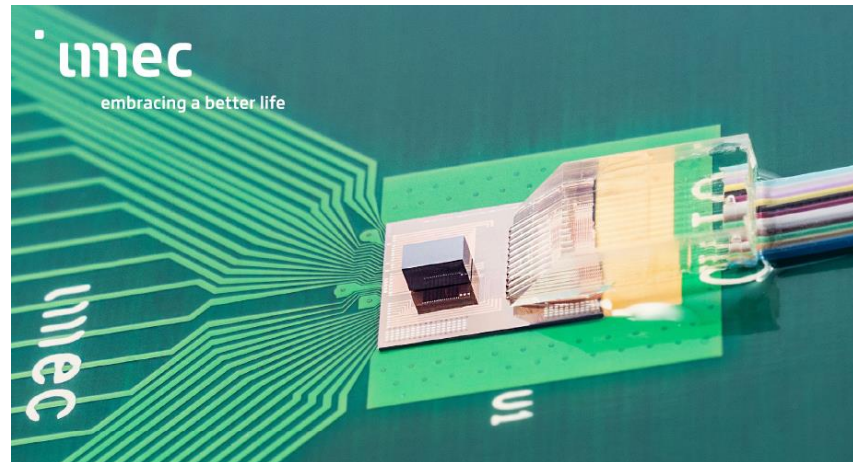
Intel Si Photonics platform announced 400 Gb/s transmission in 2019



Intel 100G CWDM4 QSFP28

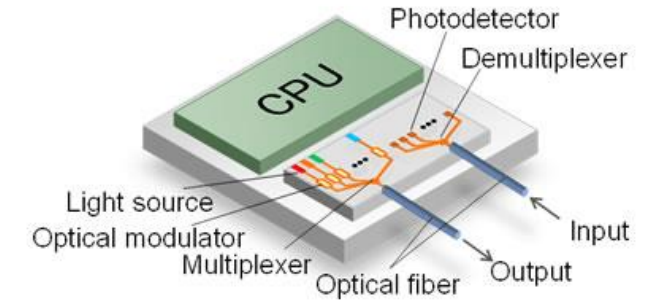


## On-board Optics



Intel Co-packaged 12.8 Tb/s Switch (2020)  
SiPh engine @ 1.6 Tb/s

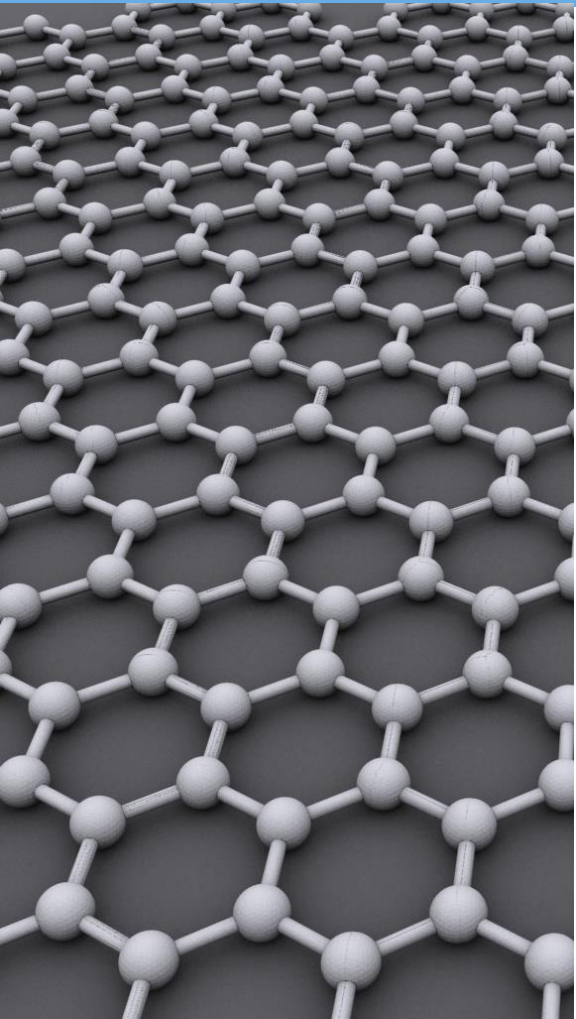
## Co-packaged Optics



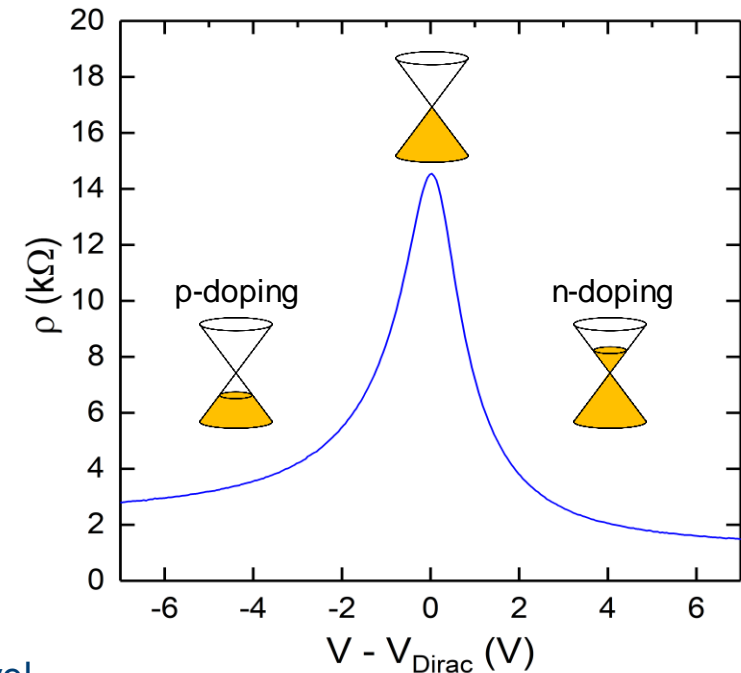
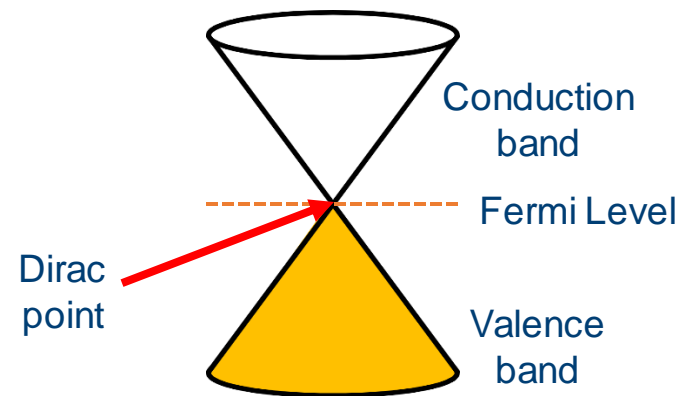
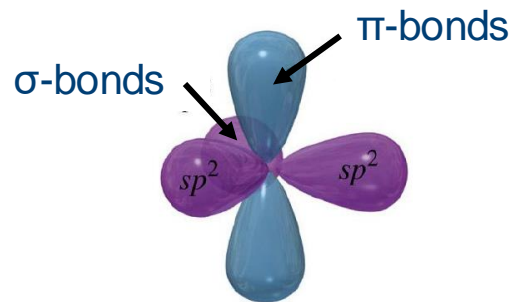
Tanaka, S et al. *Fujitsu Scientific and Technical Journal*, **50(1)**, 123–131, (2014)



# Graphene: Electrical Properties



- Strong in-plane  $\sigma$ -bonds between C atoms
- Carriers become delocalised by overlapping out-of-plane  $\pi$ -bonds
- In-plane confinement leads to a linear band structure

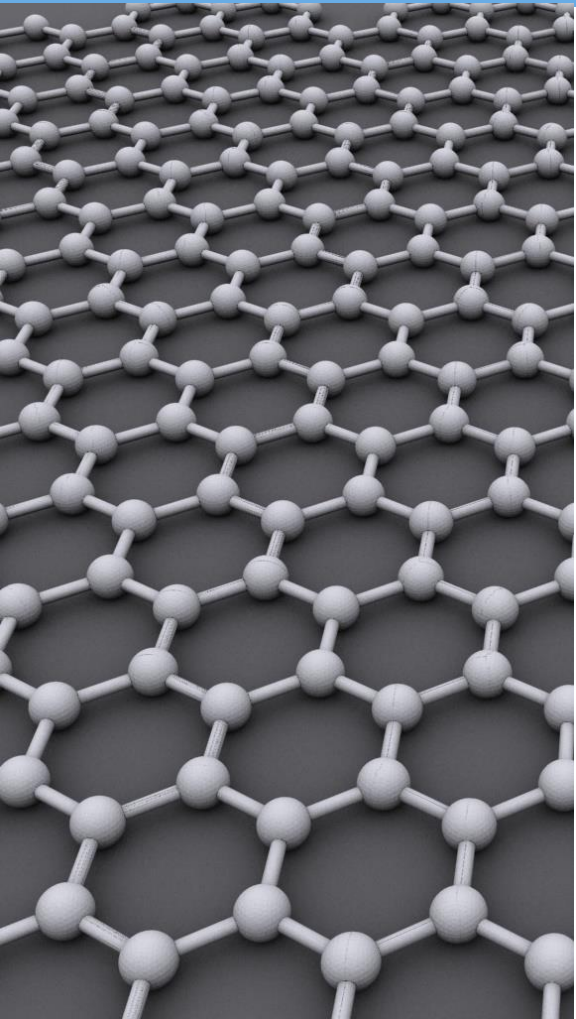


High carrier mobility  
( $>100,000$  cm<sup>2</sup>/Vs) at  
room temperature

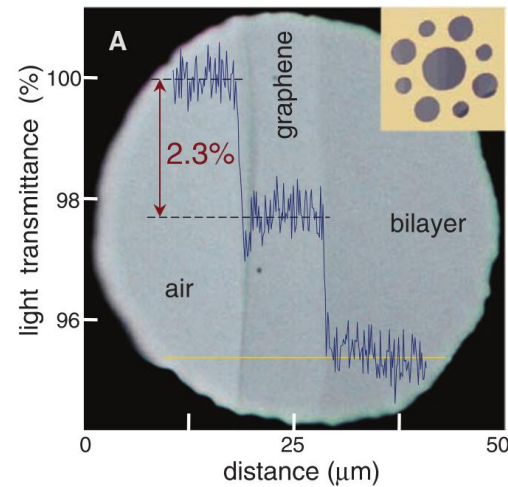
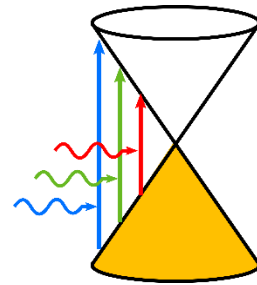




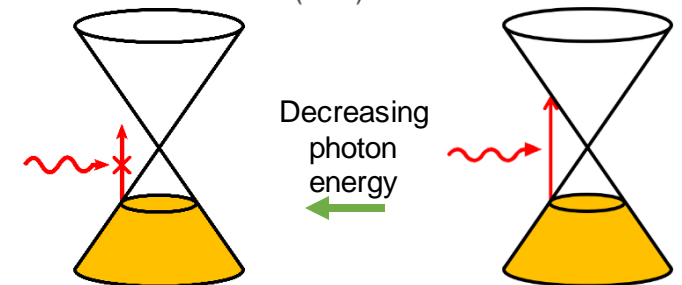
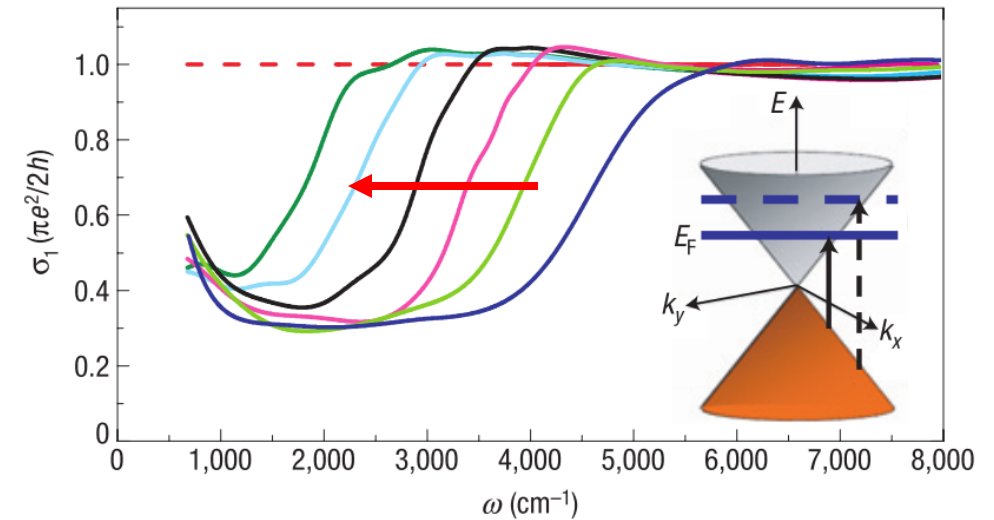
# Graphene: Optical Properties



## Wavelength independent absorption



## Electrostatically tuneable optical conductivity

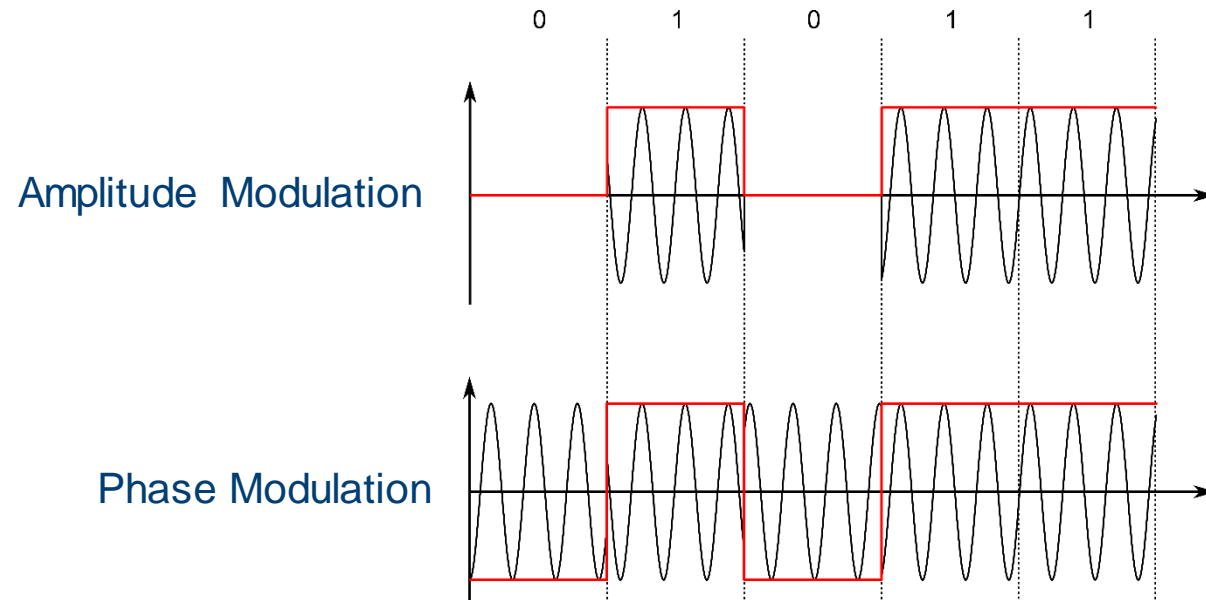


Nair, R. R., et al. *Science*, 320(5881), 1308–1308 (2008)

Li, Z. et al. *Nature Physics*, 4(7), 532–535 (2008)

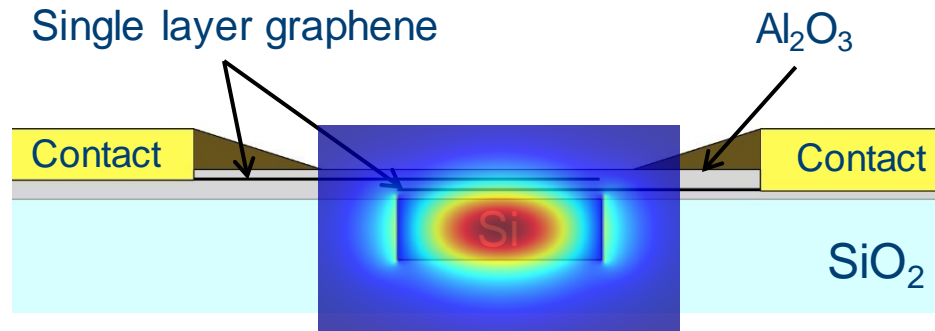


# Integrated Modulators

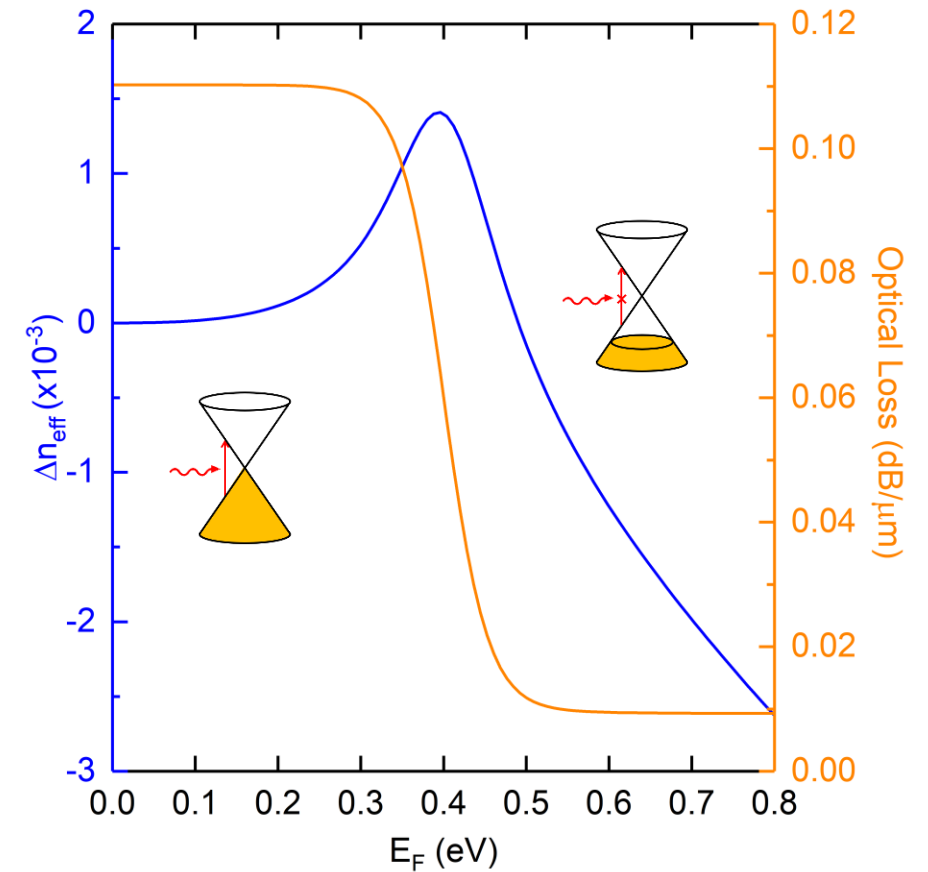


- Converts electrical data stream into an optical signal
- Encodes information in the amplitude and/or phase of the optical signal
- Typically uses Si, Lithium Niobate, or III-V material

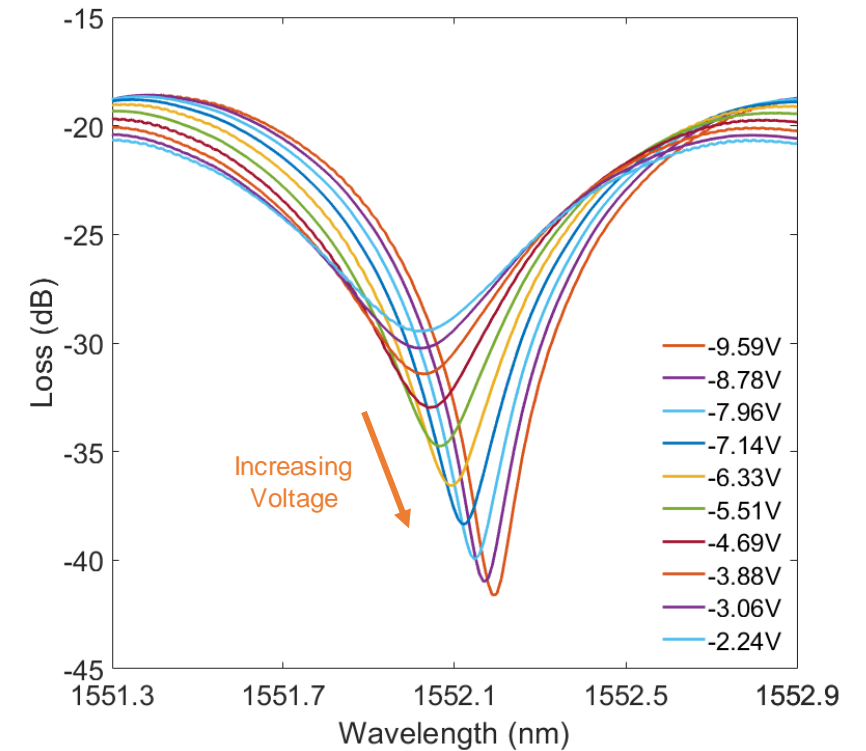
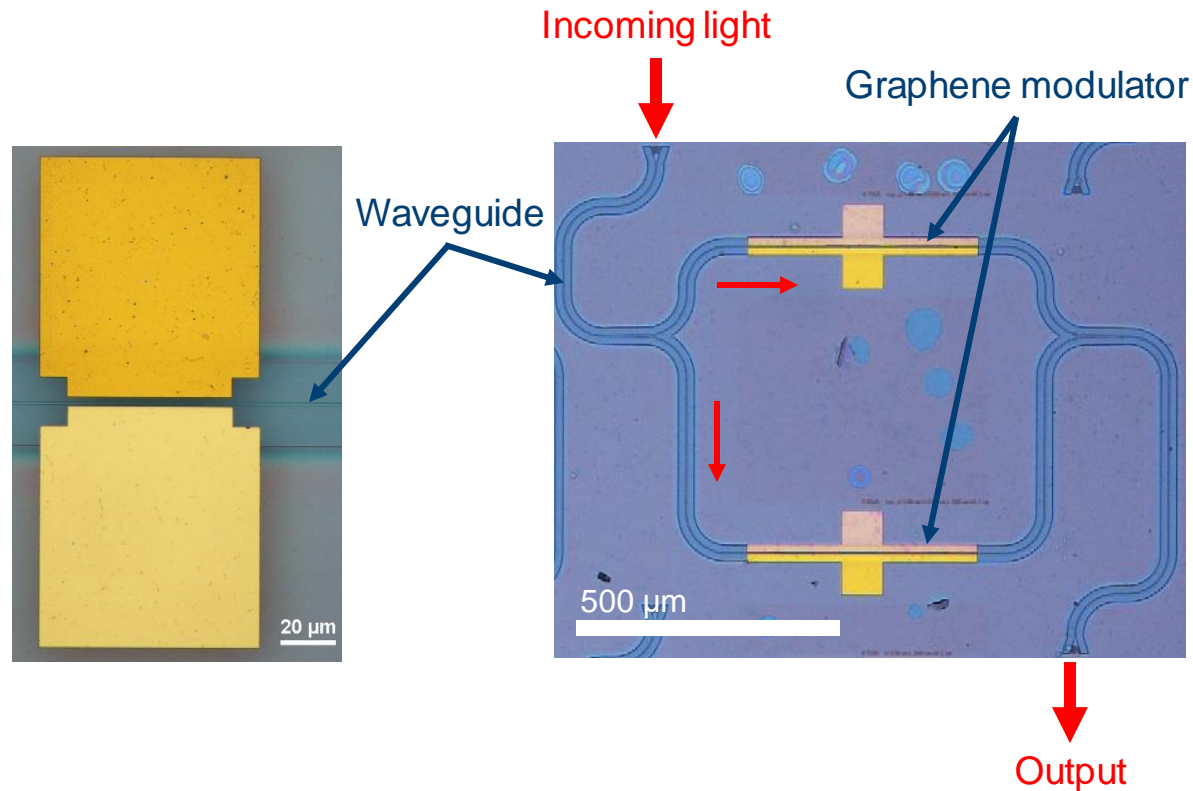
# Graphene Modulators



- Applied voltage changes the doping of each SLG and therefore the optical conductivity
- Changes the refractive index and optical losses of the propagating light
- Can be used as a phase or amplitude modulator



# Graphene Phase Modulator

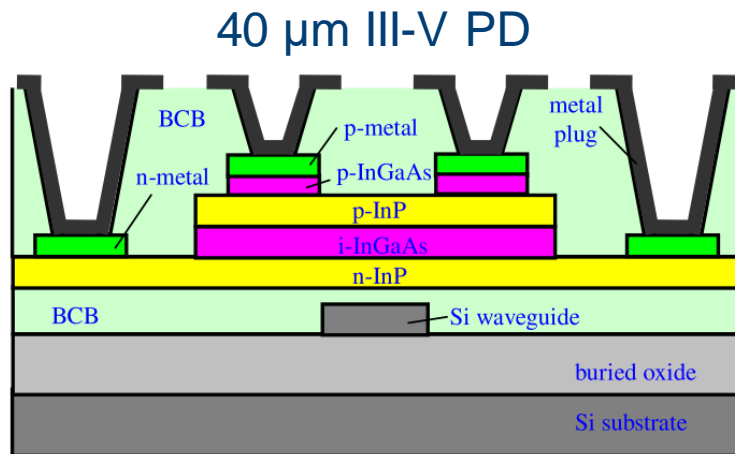
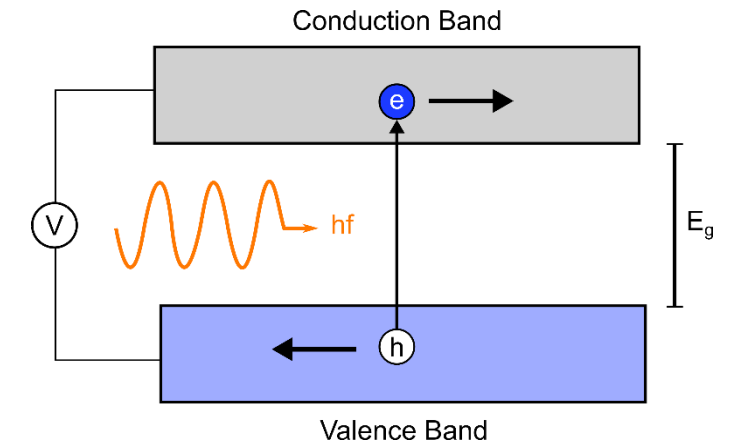


- Millimetre device length for  $\pi$ -phase shift in  $V_{\text{DD}} = 1\text{V}$
- >20 GHz bandwidth

Watson, H. F. Y., *et al.* (2020) Manuscript in preparation

# Integrated Photodetectors

- Converts an optical signal back into an electrical signal at the receiver
  - Photons are absorbed and produce an electron-hole pair
  - Electron-hole pairs are separated by an electric field and generate a photocurrent
- Limited by carrier recombination and dark current



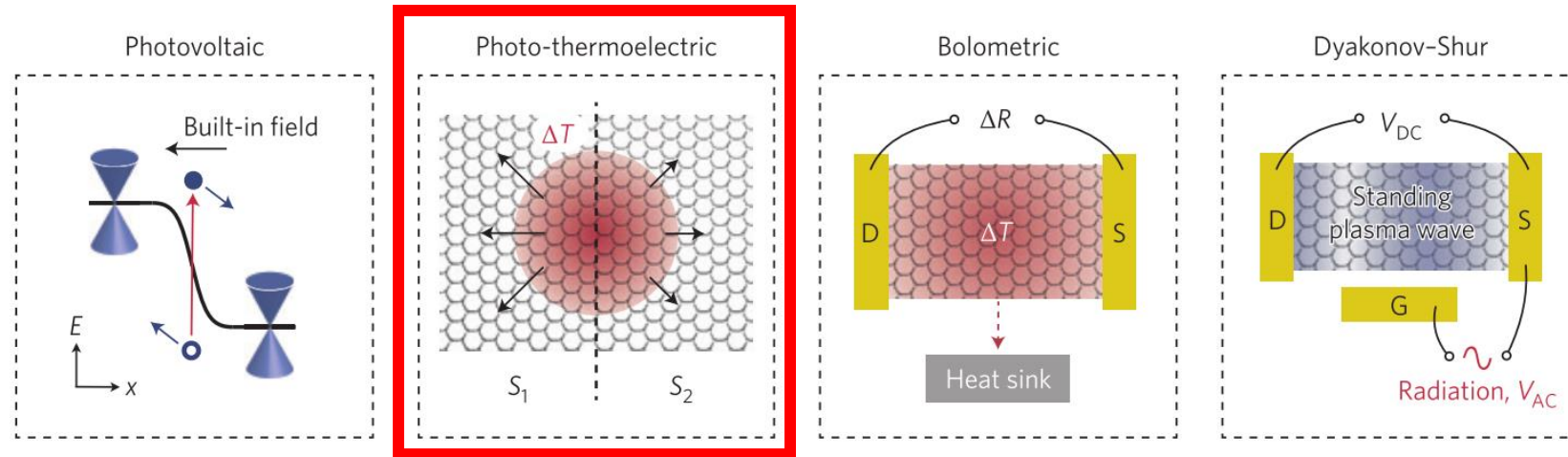
Sheng, Z., et al. *Optics Express*, 18(2), 1756 (2010)

- Typically use p-i-n junctions based on Ge-on-Si or bonded III-V wafers





# Graphene Photodetectors



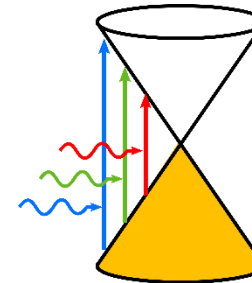
Koppens, F. H. L., *et al. Nature Nanotechnology*, 9(10), 780–793 (2014)

## Advantages

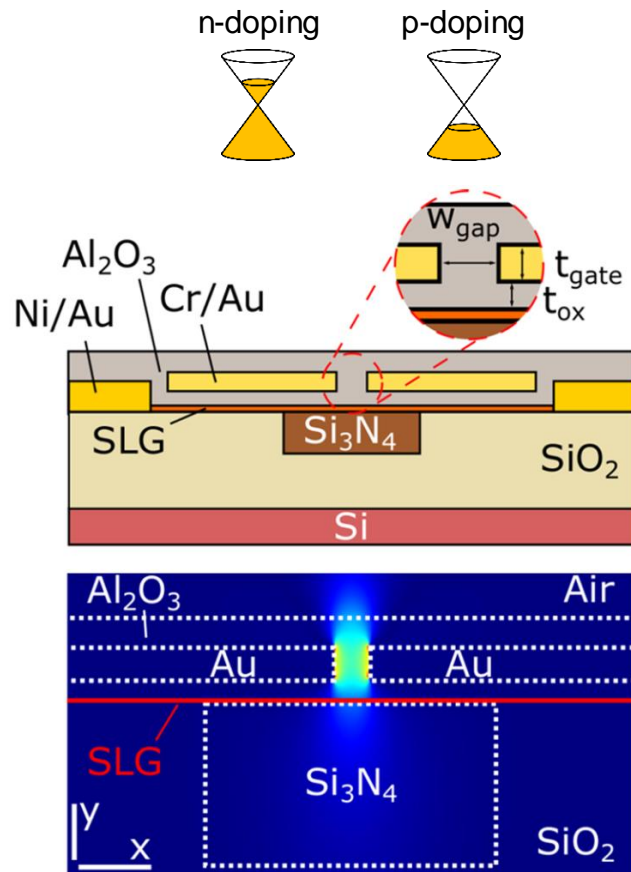
- Wavelength independent absorption
- High mobility = fast operation

## Disadvantages

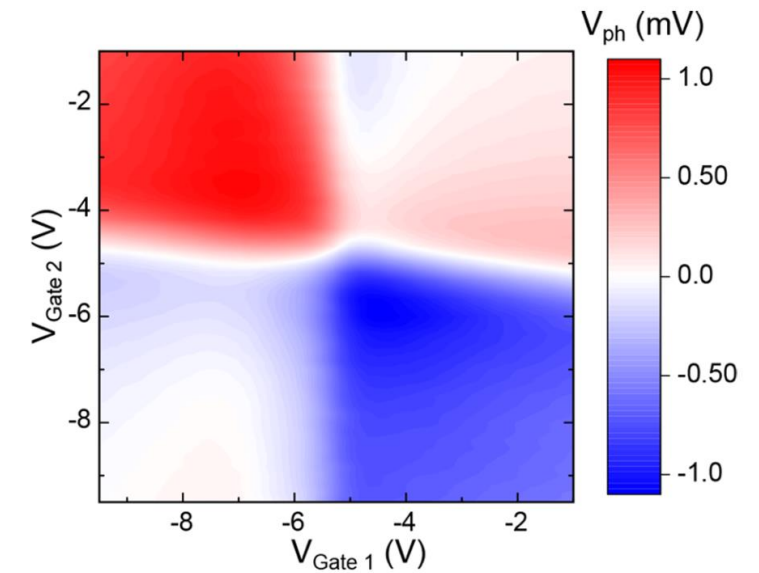
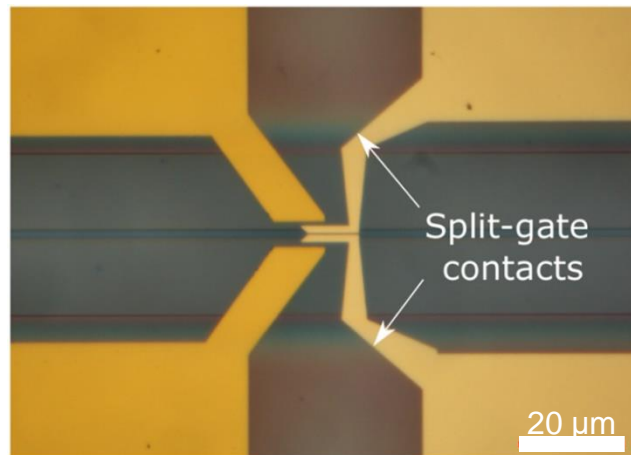
- Limited by dark current because of a zero band gap



# Graphene PTE Photodetector



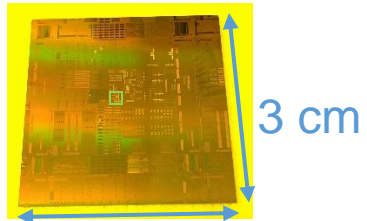
- Split-gates used to create a p-n junction in the SLG channel
- Efficiency increased due to plasmonic-enhanced optical field
- 12.2 V/W, 42 GHz bandwidth
- Zero bias operation = zero dark current



Muench, J. E., et al. *Nano Letters*, 19(11), 7632–7644 (2019).



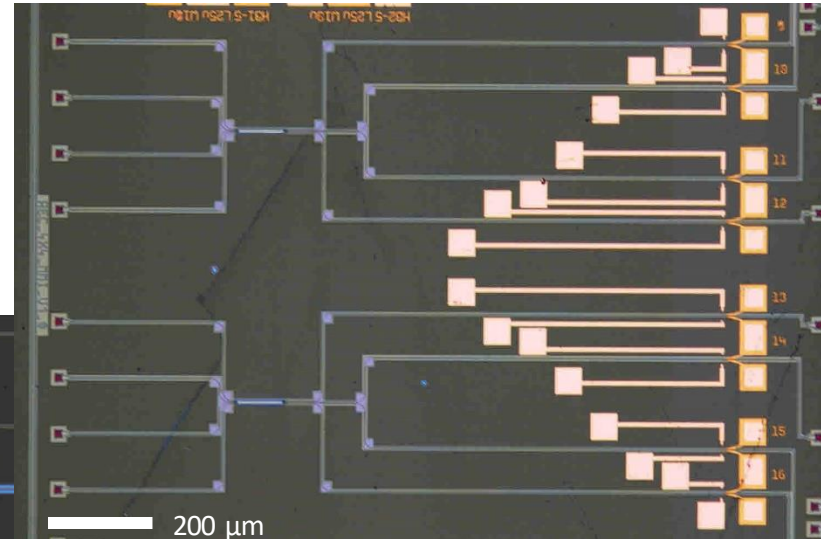
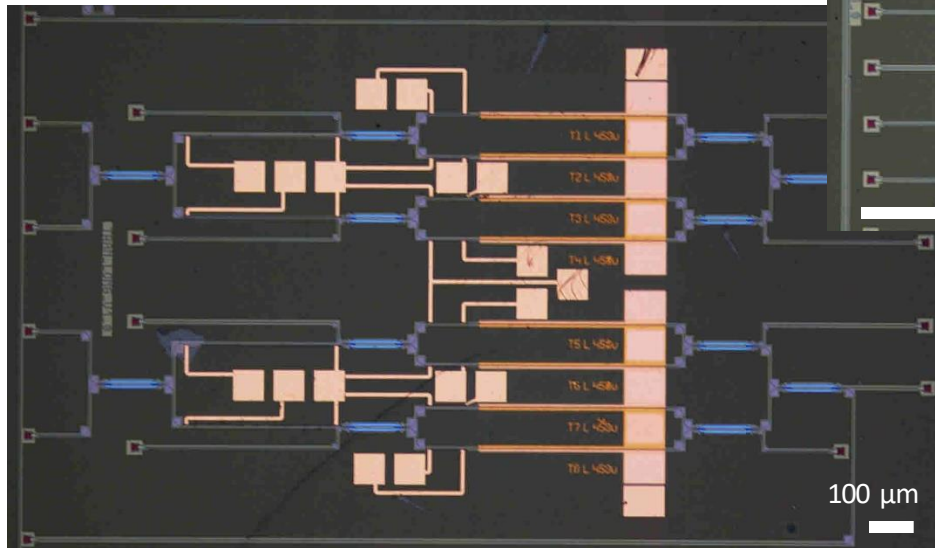
# Graphene IQ Transceiver



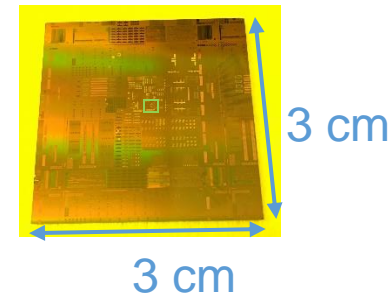
3 cm

3 cm

Graphene Transmitter

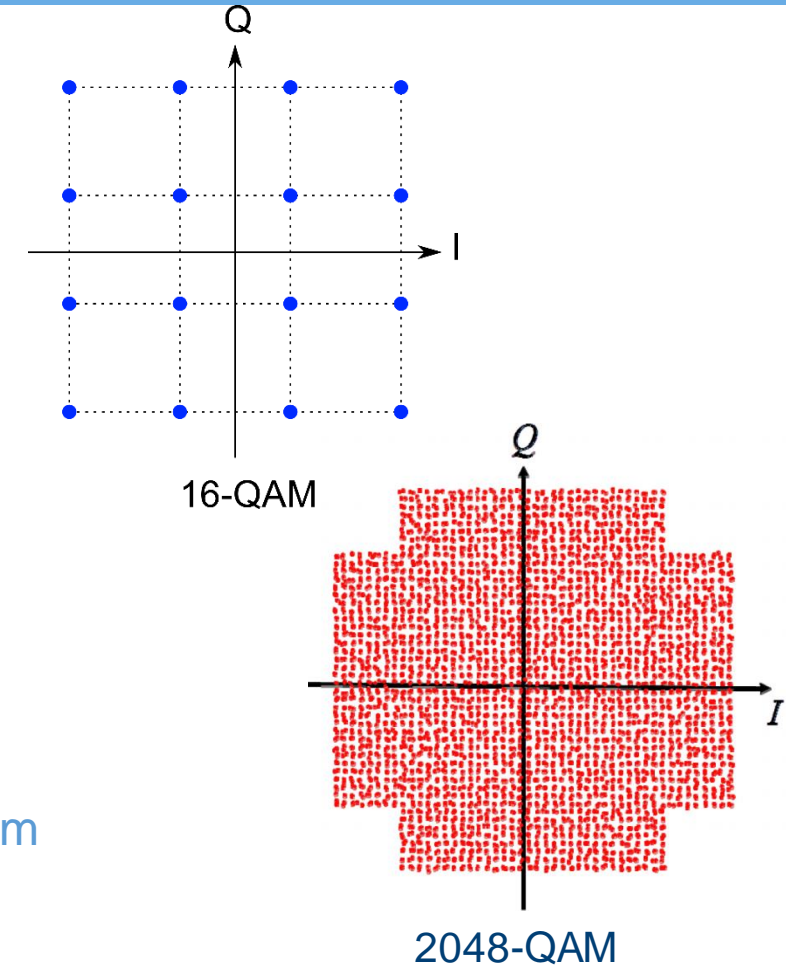


Graphene Receiver



3 cm

3 cm



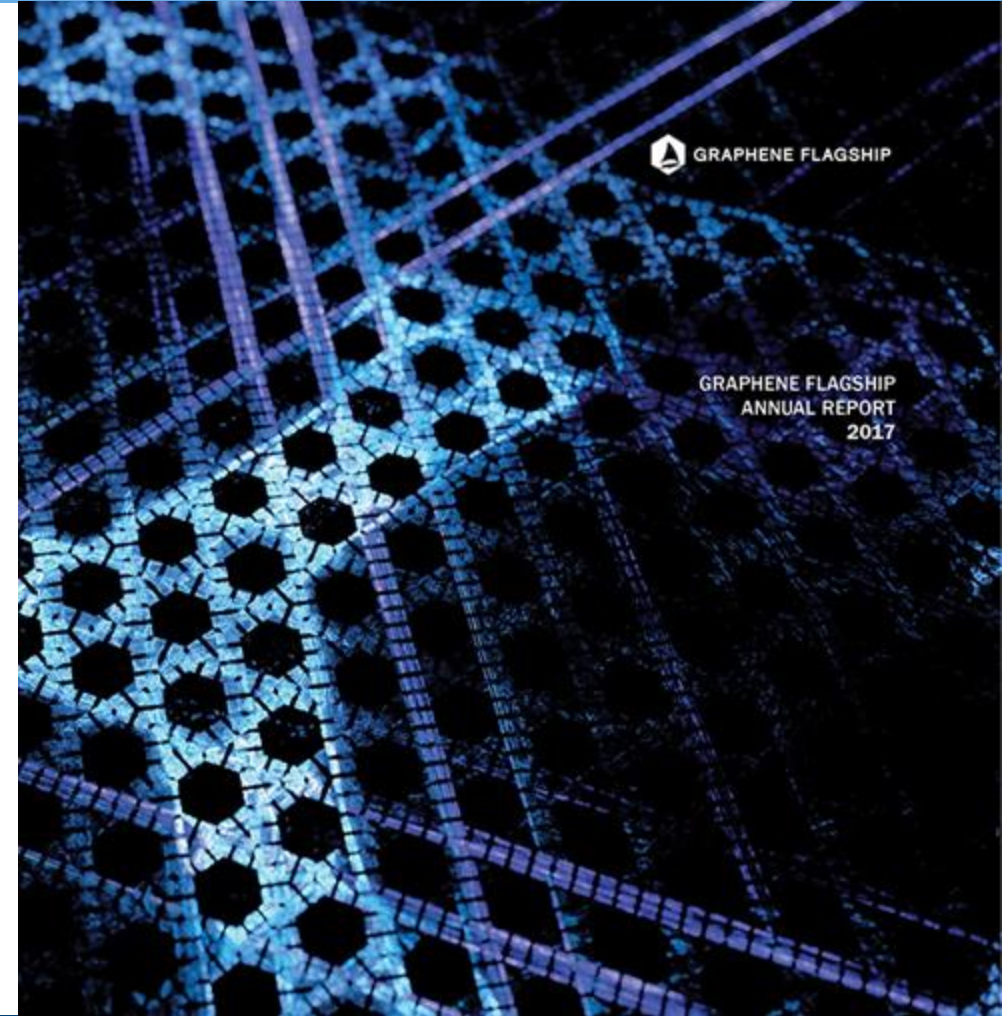
Beppu, S, et al. *Optics Express*, 23(4), 4960-4969 (2015)





# Outlook

- Power efficiency is key for Tb/s data transmission
- Si Photonics technology enables integrated photonic circuits
- Graphene offers a combined and efficient modulation and photodetection platform that can be fabricated in the CMOS back-end-of-line
- Work still needs to be done to improve the uniformity and mobility and reduce optical loss in order to realise simulated device performances



# Acknowledgements



Wolfson College  
Cambridge



UNIVERSITY OF  
CAMBRIDGE



# Back up Slides

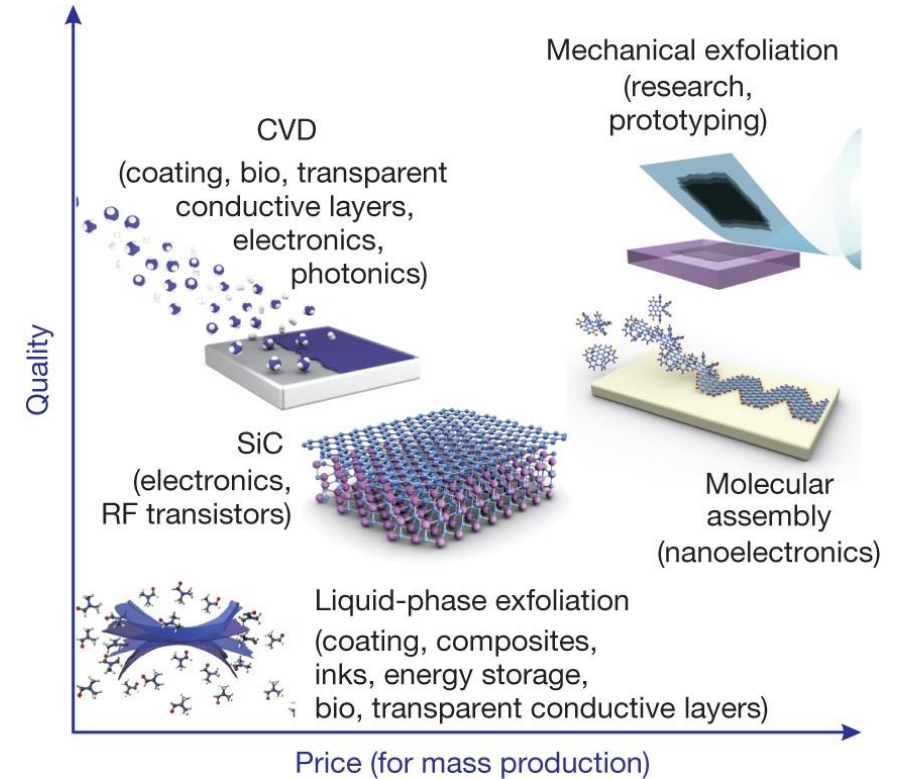


# Graphene Production

- Best electrical properties from mechanical exfoliation (Scotch tape method)
- Worst electrical properties from liquid phase exfoliation
- Combination of good electrical properties and scalability is chemical vapour deposition (CVD)



- Large area growth up to 30 inch films (roll-to-roll)
- Can be transferred onto any substrate



Novoselov, K *et al.* *Nature* **490**, 192–200 (2012)



# Mach Zehnder Interferometer

- To detect a change of phase in an optical signal an interferometric device is required
- Usually this is with a Mach-Zehnder interferometer or ring resonator

